

# Wideband Distributed Amplifier, DIE

## 0.75 - 22 GHz



ENGDA00073

Rev. V1

### Features

- Wideband Performance
- High Linearity
- Positive Gain Slope: 2.5 dB
- Excellent Return Loss: 20 dB
- Die Size:
  - 4.78 x 2.46 x 0.1 mm
  - 0.188 x 0.097 x 0.004 inch
- RoHS\* Compliant

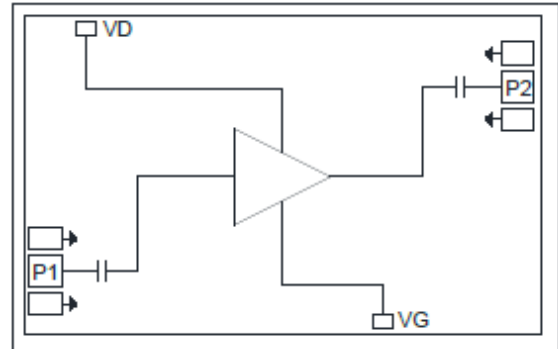
### Applications

- Military EW & SIGINT
- Receiver or Transmitter
- Telecom Infrastructure
- Space Hybrids
- Test & Measurement Systems

### Description

The ENGDA00073 is a wideband GaAs MMIC distributed amplifier die which operates from 0.75 to 22 GHz. The design is 50 ohm matched and includes on board bias circuitry. The amplifier delivers 10 dB gain at 21 GHz with 1 dB of positive gain slope across the full band. The amplifier is extremely linear with OIP3 near 15 dB better than OP1dB. The MMIC has gold backside metallization and is designed to be silver epoxy attached. The RF interconnects are designed to account for wire bonds and external microstrip flares for optimal integrated return loss. No additional ground interconnects are required.

### Functional Block Diagram



### Ordering Information

Part Number	Package
ENGDA00073	Die

\* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

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**Electrical Specifications:  $T_A = +25^\circ\text{C}$ ,  $V_D = 8\text{ V}$ ,  $V_G = -1.1\text{ V}$ ,  $Z_0 = 50\ \Omega$**

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Gain	0.7 - 10 GHz 10 - 22 GHz	dB	7.0 8.5	9.0 10.0	—
Noise Figure	0.7 - 10 GHz 10 - 22 GHz	dB	—	5 6	—
Input / Output Return Loss	0.7 - 22 GHz	dB	15	20	—
Output P1dB	0.7 - 22 GHz	dBm	16.5	18.0	—
Output IP3	0.8 - 10 GHz 10 - 20 GHz	dBm	35 28	40 36	—
Output IP2	0.8 - 10 GHz 10 - 20 GHz	dBm	38 38	48 46	—
Supply Current	0.8 - 20 GHz	mA	120	152	180
Thermal Resistance	0.8 - 20 GHz	$^\circ\text{C/W}$	—	37	—

### Recommended Operating Conditions

Parameter	Min.	Typ.	Max.	Units
Drain Voltage	6.5	8.0	10.5	V
Gate Voltage	-0.6	-1.1	-1.4	V
Drain Current	—	152	—	mA

### Absolute Maximum Ratings<sup>1,2</sup>

Parameter	Absolute Maximum
Drain Voltage	12 V
Gate Voltage	-6 V
RF Input Power	25 dBm
Junction Temperature	+160 $^\circ\text{C}$
Operating Temperature	-55 $^\circ\text{C}$ to +100 $^\circ\text{C}$
Storage Temperature	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$

1. Exceeding any one or combination of these limits may cause permanent damage to this device.
2. MACOM does not recommend sustained operation near these survivability limits.

### Handling Procedures

Please observe the following precautions to avoid damage:

### Static Sensitivity

These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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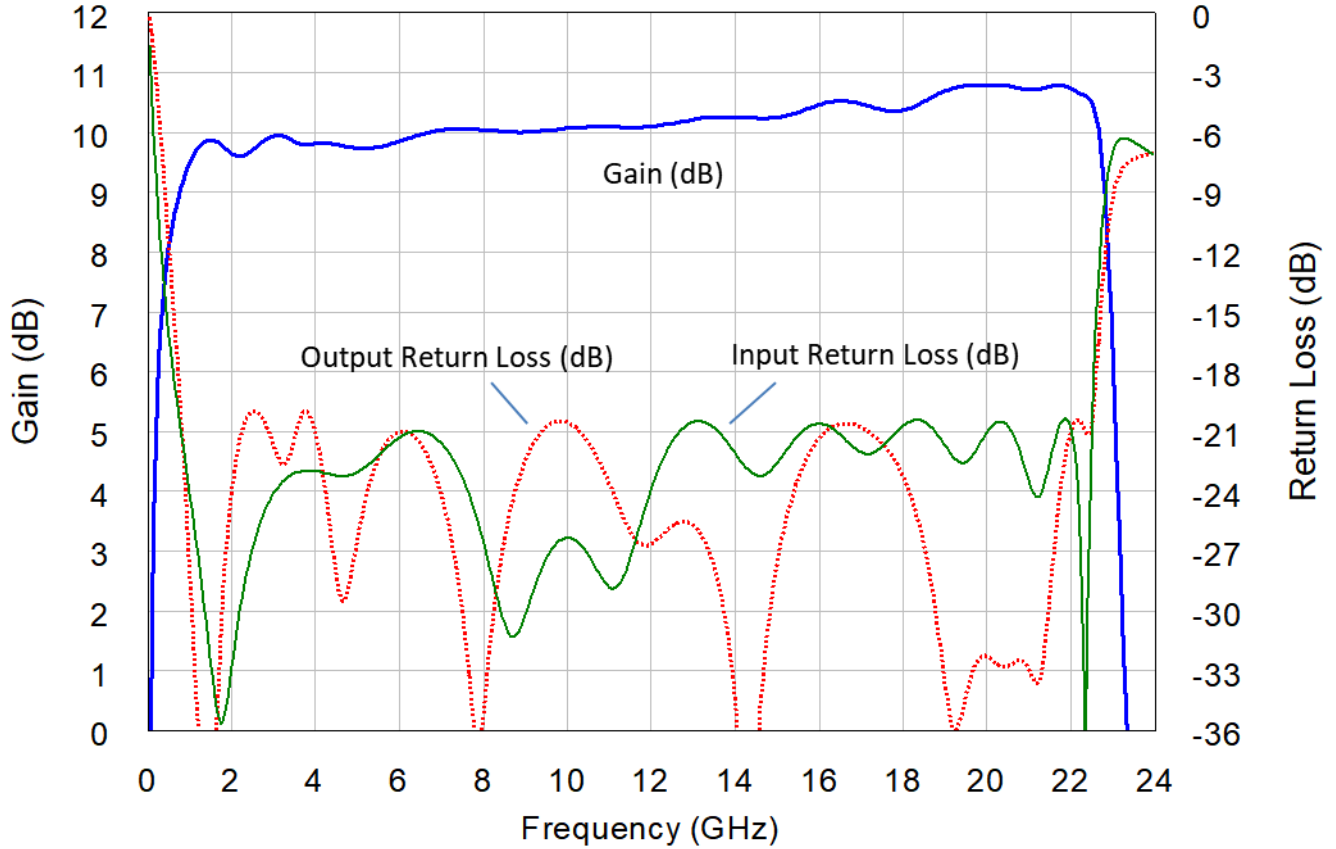


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### Measured RF Data with Wirebonds & External Microstrip Flares

Gain and In / Out Return Loss:  $V_D = 8\text{ V}$ ;  $V_G = -1.1\text{ V}$ ;  $I_D = 152\text{ mA}$



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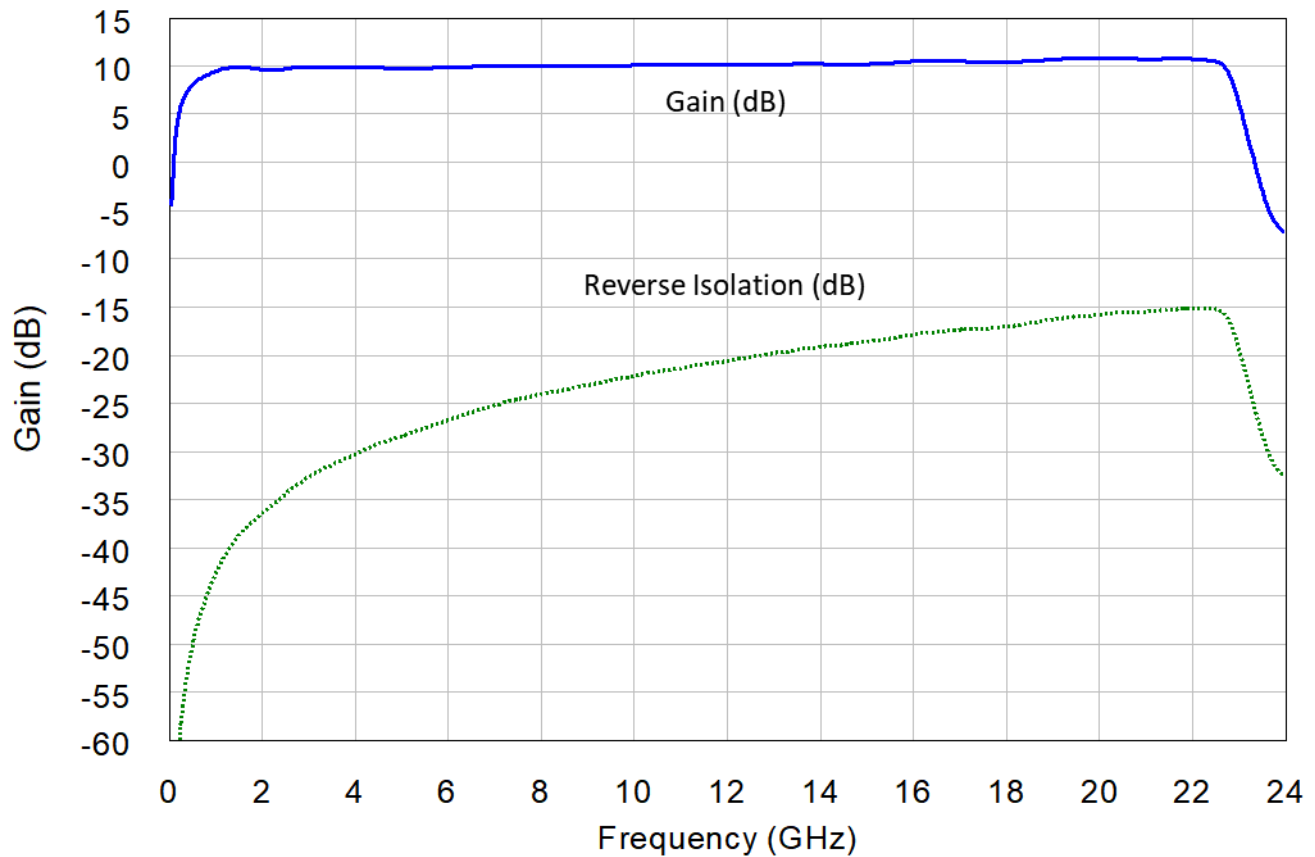


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### Measured RF Data with Wirebonds & External Microstrip Flares

Gain and Reverse Isolation:  $V_D = 8\text{ V}$ ;  $V_G = -1.1\text{ V}$ ;  $I_D = 152\text{ mA}$



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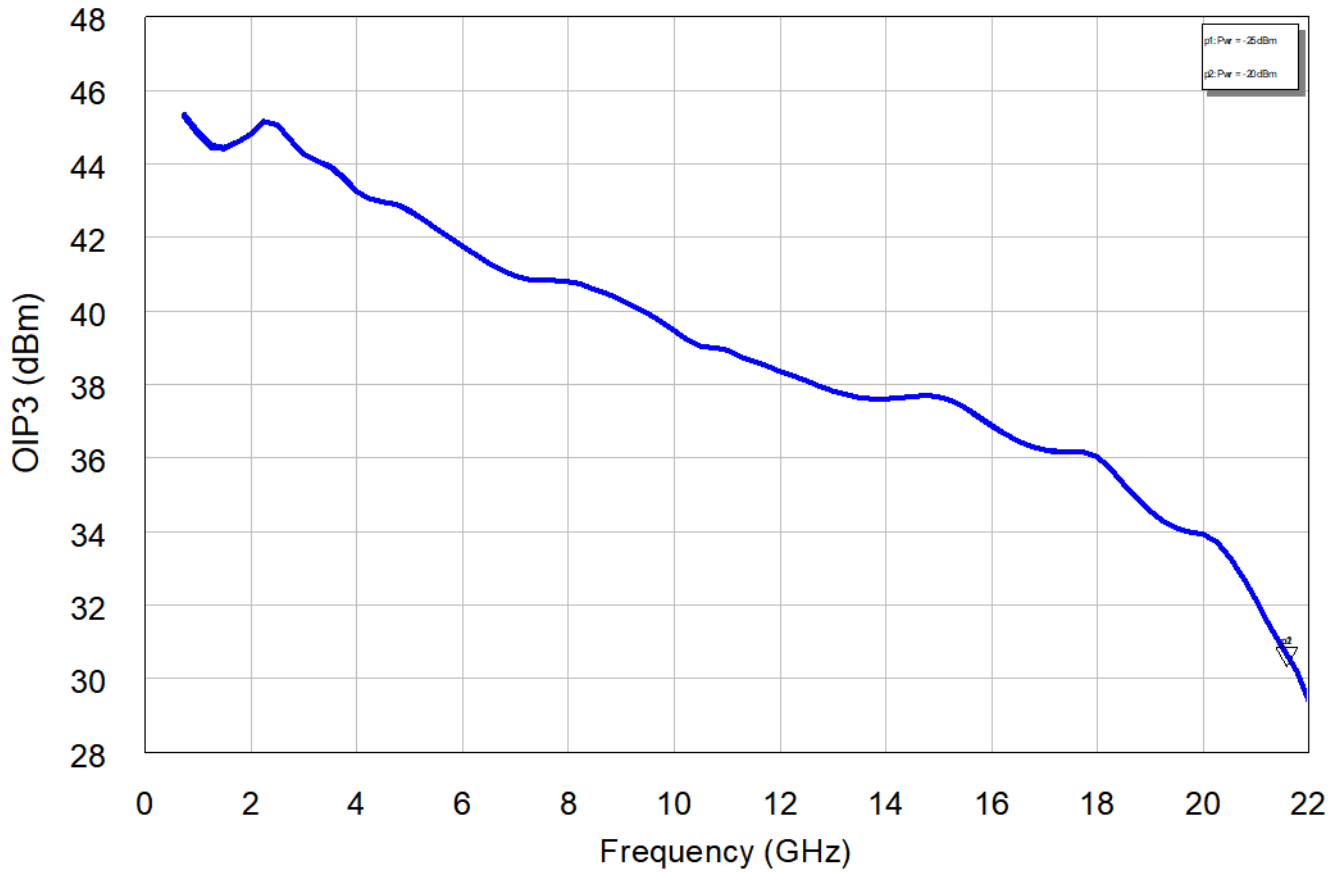


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### Measured RF Data with Wirebonds & External Microstrip Flares

*OIP3 and OP1dB ~ 18 dBm:  $V_D = 8\text{ V}$ ;  $V_G = -1.1\text{ V}$ ;  $I_D = 152\text{ mA}$ ,  $OIP3 > 36\text{ dBm}$  to 18 GHz*



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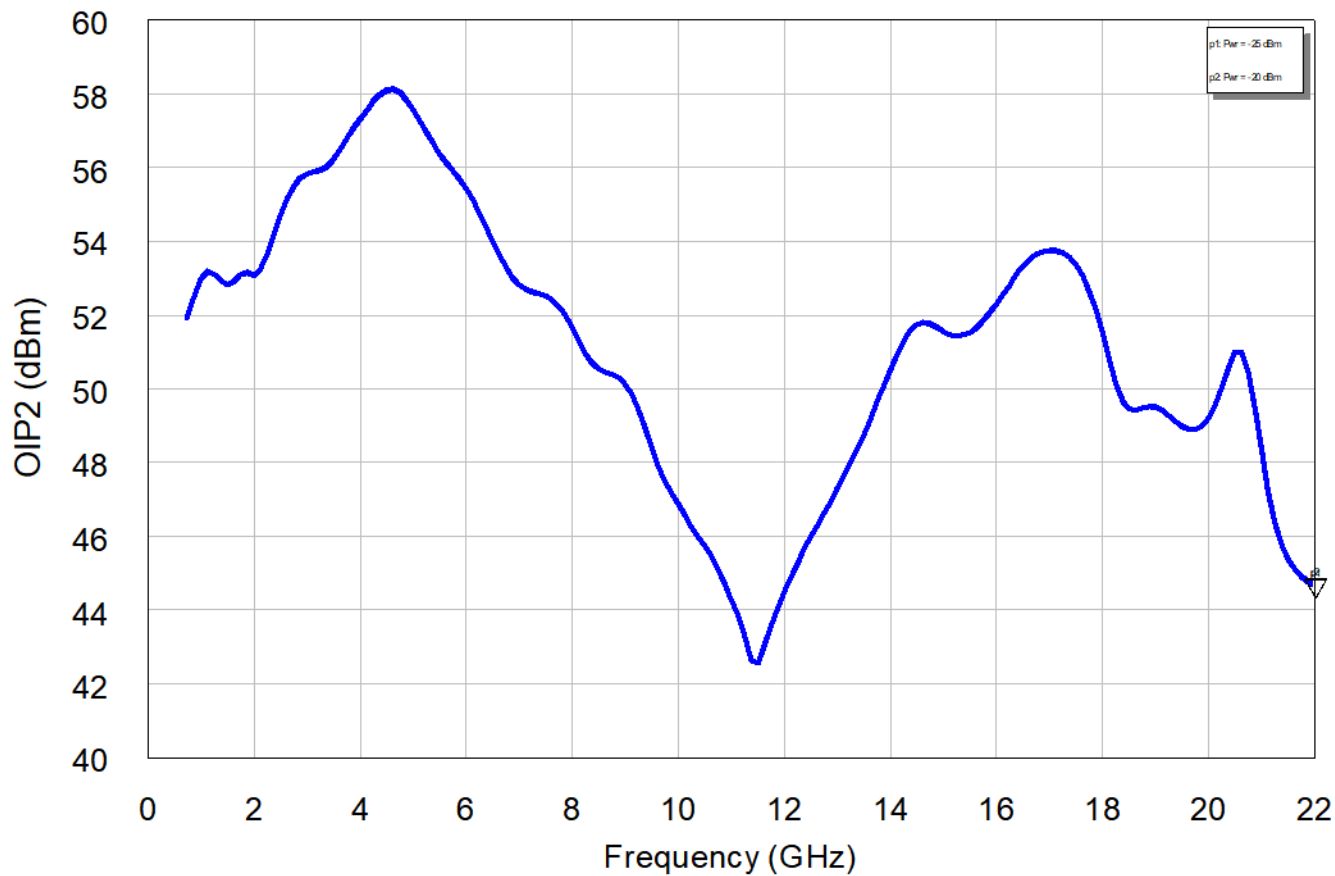


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### Measured RF Data with Wirebonds & External Microstrip Flares

*OIP2 and OP1dB ~ 18 dBm:  $V_D = 8\text{ V}$ ;  $V_G = -1.1\text{ V}$ ;  $I_D = 152\text{ mA}$ , OIP2 >42 dBm*



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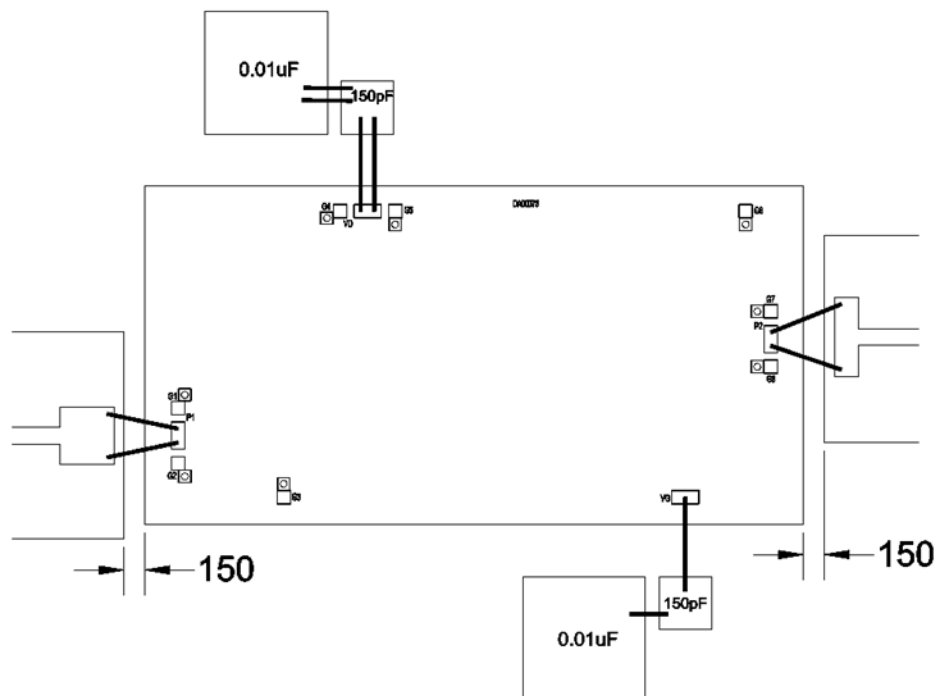
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### External I/O Microstrip Flare Dimensions (on 5-mil Alumina) and I/O Bond Wire Inductances for Optimum Insertion and Return Loss Performance

S-parameters can be supplied at DIE level such that optimal flare dimensions can be made for the substrate connection medium used (if different from 5-mil Alumina).

Pad Flare Dimension	Flare Width x-dim, ( $\mu\text{m}$ )	Flare Length y-dim, ( $\mu\text{m}$ )	Wire Inductance	Wire Length ( $\mu\text{m}$ )	# of Wires
RF Input	360	416	0.28	584	2
RF Output	175	576	0.31	660	2



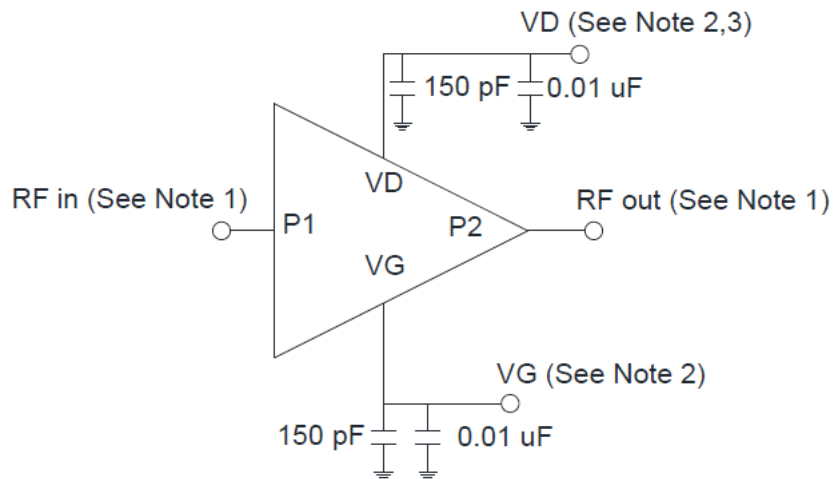
#### Notes:

- To achieve bond wire inductance noted, bond the number of wires shown in parallel from each external flare to each associated MMIC RF bond pad as shown above.
- Gold Wire Details:
  - Diameter: 25.4  $\mu\text{m}$  (1 mil)
  - Spacing: 4 mils ( $\sim 100 \mu\text{m}$ ) typical
  - Height above Ground: 8 mils ( $\sim 200 \mu\text{m}$ ) typical (wedge bonds)
- Wire Length is total length if the wire were made perfectly straight.

### Assembly Guidelines

The backside metallization is RF/DC ground. Attachment should be accomplished with electrically and thermally conductive epoxy only. Eutectic Attach is not recommended though product can be made that supports. This device supports high frequency performance. Care should be made to following the wirebond dimensions as shown in the flare diagram.

### Application Circuit and Turn-on Procedure



1. Internal blocking capacitors on RF in/out ports (P1 and P2).
2. Gate Voltage ( $V_G$ ) must be applied prior to Drain Voltage ( $V_D$ )
3. Drain Voltage ( $V_D$ ) must be removed prior to Gate Voltage ( $V_G$ ).
4. Performance is optimized with  $V_D$  set to 8 V.



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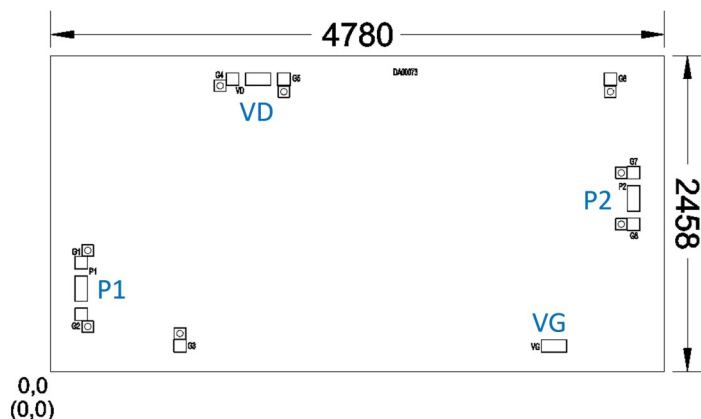
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### Outline Drawing



### Pad Dimensions

Pad Dimension	Length x-dim, (μm)	Width y-dim, (μm)	Length x-dim, (mils)	Width y-dim, (mils)
RF Input	100	200	3.9	7.9
RF Output	100	200	3.9	7.9
Drain Bias	200	100	7.9	3.9
Gate Bias	200	100	7.9	3.9

### Bond Pad Center Point Locations

Pad Location	x-dim, (μm)	y-dim, (μm)	x-dim, (mils)	y-dim, (mils)
RF Input	240	646	9.4	25.4
RF Output	4540	1346	178.7	53
Drain Bias	1617	2273	63.7	89.5
Gate Bias	3921	201	154.4	7.9

#### Notes:

All dimensions are given in both μm and mils.  
 Substrate thickness: 100 μm (0.004").  
 Backside metallization is gold.  
 Bond pad metallization is gold.

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